

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of

Noboru ICHINOSE, et al



Serial No.: 10/567,369

Group Art Unit: 2814

Filed: May 15, 2006

Examiner: Salerno, Sarah Kate

For: SEMICONDUCTOR LAYER WITH A Ga_2O_3 SYSTEM

Honorable Commissioner of Patents
Alexandria, Virginia 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sirs:

Under the provisions of 37 CFR §1.97 through §1.98 and pursuant to Applicants' duty of disclosure under 37 CFR §1.56, Applicants respectfully bring the following documents cited in the Chinese Office Action in a counterpart foreign application and listed on the attached form PTO-1449, to the attention of the Examiner in charge of the above-identified application.

This citation does not constitute an admission that the references relevant or material to the claims. It is only cited as constituting related art of which Applicants are aware.

In compliance with the concise explanation requirement under 37 CFR §1.98(a)(3) for foreign language documents, Applicants enclose herewith a copy of the Chinese Office Action citing such document, together with an English-language version (if not already included) of that portion of the Office Action indicating the degree of relevance found by the foreign office. Further, an English-language abstract is attached to the Japanese reference.

I hereby certify that each item of information contained in this Information Disclosure Statement was the first citation of that item by a foreign patent office in a counterpart foreign application, which occurred not more than three months prior to the filing of this statement.

Please charge any deficiencies in fees and credit any overpayment of fees to Attorney's Deposit Account No. 50-0481.

Respectfully submitted,

Date: 06/16/09

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